

**Listing of Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-6. (Canceled)

7 (Previously presented) A method of manufacturing a microelectronic device, comprising:

performing a first inspection of a device feature during an intermediate stage of manufacture;  
cleaning the device feature after the first inspection; and  
performing a second inspection of the device feature after cleaning the device feature, wherein the device feature is located in a production region of a wafer, the wafer further including a calibration region having a calibration feature located therein.

8. (Original) The method of claim 7 wherein the calibration feature comprises a first conductive layer located over the wafer, a buffer layer located over the first conductive layer, and a second conductive layer located over the buffer layer.

9. (Original) The method of claim 8 wherein the first conductive layer comprises AlCu, the second conductive layer comprises W, and the buffer layer comprises:

a first TiN layer over the first conductive layer;  
an implanted Ti layer over the first TiN layer; and  
a second TiN layer over the implanted Ti layer.

Claims 10-22. (Canceled)

23. (Currently amended) The method of claim [[2]] 7 wherein at least one of the first and second inspections is performed by a scanning electron microscope (SEM).

24. (Currently amended) The method of claim [[2]] 7 wherein the cleaning comprises exposing the device feature to an oxygen containing plasma.

25. (Currently amended) The method of claim ~~[[2]]~~ 7 wherein the device feature comprises a first conductive layer located over a substrate, a buffer layer located over the first conductive layer, and a second conductive layer located over the buffer layer.